

### **CT Micro**

### **Features**

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Temperature range 55 °C to 110 °C

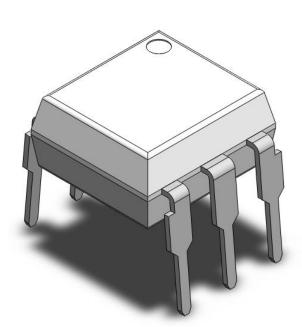
## **Applications**

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

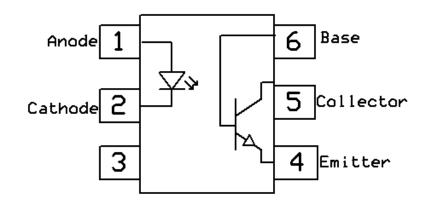
### Description

The CNY17-X and CNY17F-X series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 6-lead DIP package with bending options.





Schematic



Note: CNY17-F without Base Connection

Note: Different bending options available. See package

dimension.



# Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	VRMS	
Topr	Operating temperature	-55 ~ +110	°C	
Тѕтс	Storage temperature	-55 ~ +125	°C	
Tsol	Soldering temperature	260	°C	
Emitter			·	
l <sub>F</sub>	Forward current	60	mA	
F(TRANS)	Peak transient current (≤1µs P.W,300pps)	1	А	
VR	Reverse voltage	6	V	
PD	Power dissipation	100	mW	
Detector			·	
PD	Power dissipation	150	mW	
BVCEO	Collector-Emitter Breakdown Voltage	80	V	
Вусво	Collector-Base Breakdown Voltage	80	V	
B <sub>VECO</sub>	Emitter-Collector Breakdown Voltage	7	V	
BVEBO	Emitter-Base Breakdown Voltage	7	V	



### Electrical Characteristics T<sub>A</sub> = 25°C (unless otherwise specified)

#### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I⊧=10mA		1.2	1.4	V	
IR	Reverse Current	$V_R = 6V$	-	-	5	μA	
CIN	Input Capacitance	f= 1MHz	-	20	-	pF	

#### **Detector Characteristics**

Symbol	Param	eters	Test Conditions	Min	Тур	Max	Units	Notes
B <sub>VCEO</sub>	Collector-Emitter	Breakdown	Ic= 100μA	80	-	-	V	
BVECO	Emitter-Collector	Breakdown	I <sub>E</sub> = 1mA	7	•	-	V	
Вусво	Collector-Base		Ic= 100μA	80	-	-	V	
DACBO	Breakdown	CNY17-X						
Вуево	Emitter-Base		I <sub>E</sub> = 100μA	7	_		V	
DVEBO	Breakdown			Ĩ	-	-		
ICEO	Collector-Emitter Dark Current		V <sub>CE</sub> = 10V, I <sub>F</sub> =0mA	-	-	45	nA	
lana	Collector-Base	CNY17-X	V <sub>CB</sub> = 10V, I <sub>F</sub> =0mA		-	20	nA	
I <sub>CBO</sub>	Dark Current	GNT17-X				20		

### **Transfer Characteristics**

Symbol	ŀ	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
		CNY17-1,CNY17F-1	- IF= 10mA, Vce= 5V	40	-	80	%	
		CNY17-2,CNY17F-2		63	-	125		
	Current	CNY17-3,CNY17F-3		100	-	200		
стр	Current	CNY17-4,CNY17F-4		160	-	320		
CTR	Transfer Ratio	CNY17-1,CNY17F-1	- IF= 1mA, Vce= 5V	13	-	-		
		CNY17-2,CNY17F-2		22	-	-		
		CNY17-3,CNY17F-3		34	-	-		
		CNY17-4,CNY17F-4		56	-	-		
Manual	Collector- E	mitter Saturation	I <sub>F</sub> = 10mA, I <sub>C</sub> = 2.5mA			0.3	V	
$V_{CE(SAT)}$	Voltage		1F- 1011A, 10- 2.011A	-	-	0.5	v	
Rio	Isolation Resistance		V <sub>IO</sub> = 500V <sub>DC</sub>	1x10 <sup>11</sup>			Ω	
Cio	Isolation Capacitance		f= 1MHz		0.25		pF	



#### CT Micro

### Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
Ton	Turn On Time		-	9.5	11.5		
tr	Rise Time	Ic= 2mA, VCE= 10V, RL=	-	5.6	9.8	μs	
T <sub>OFF</sub>	Turn Off Time	100Ω	-	9	11.5		
t <sub>f</sub>	Fall Time		-	8	9.8	μs	



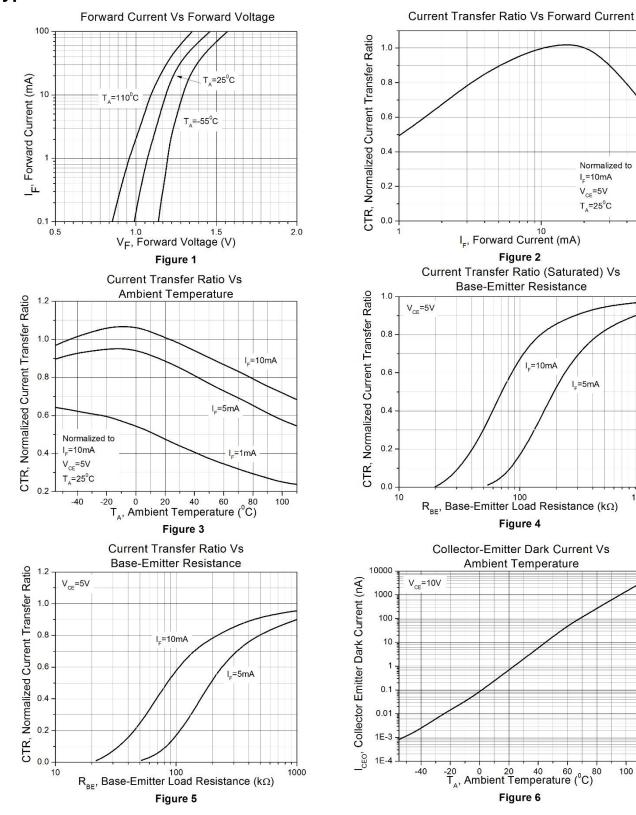
> Normalized to I<sub>F</sub>=10mA

V<sub>CE</sub>=5V T<sub>A</sub>=25<sup>0</sup>C

I\_=5mA

1000

**Typical Characteristic Curves** 

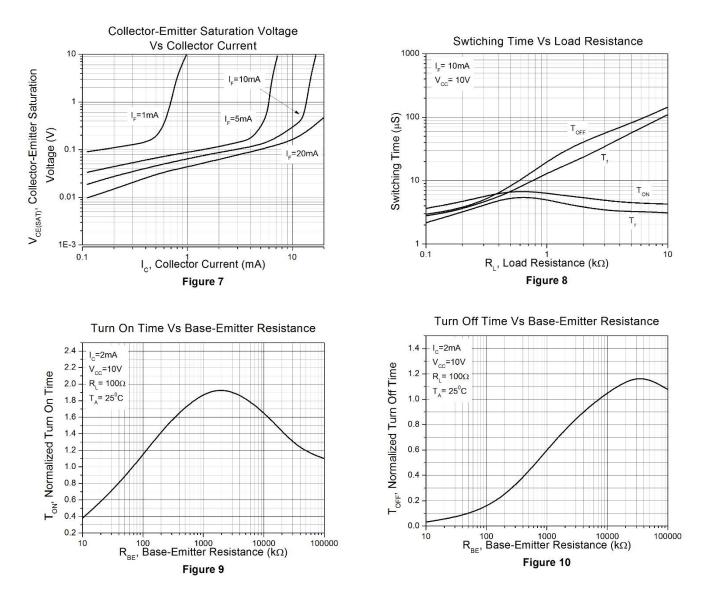


CT Micro

100



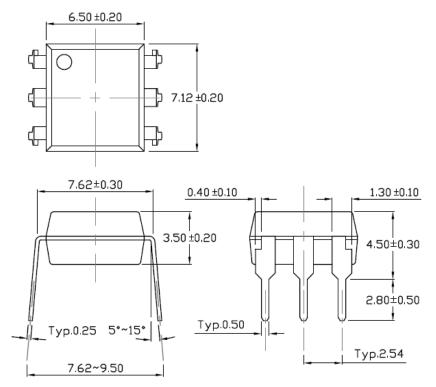
# **Typical Characteristic Curves**



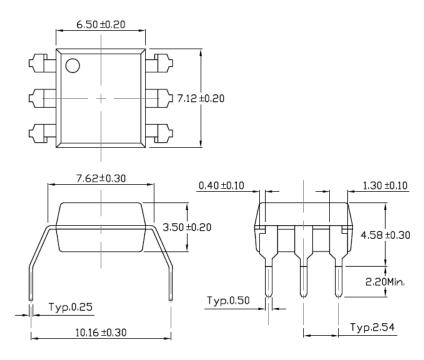


Package Dimension Dimensions in mm unless otherwise stated

### Standard DIP – Through Hole

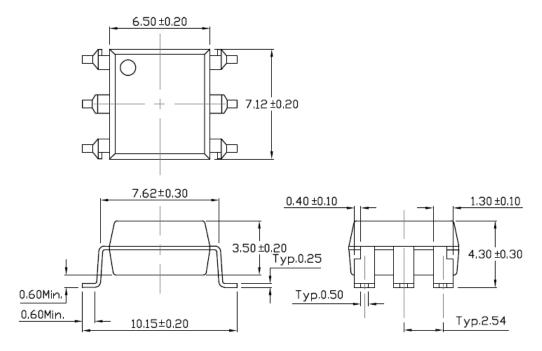


### Wide Lead Forming – Through Hole

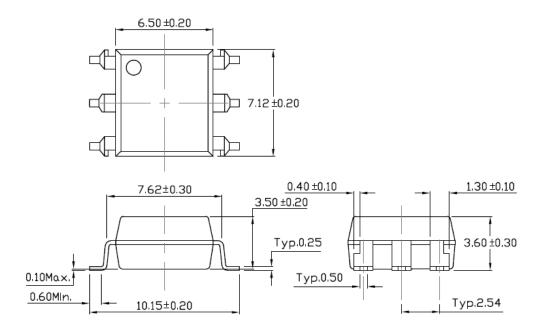




### Surface Mount Forming

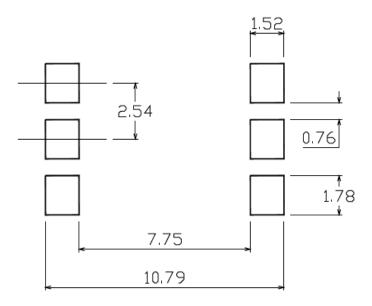


## Surface Mount Forming (Low Profile)

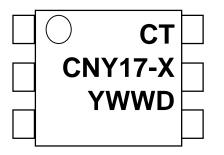




### Recommended Solder Mask Dimensions in mm unless otherwise stated



## **Marking Information**



### Note:

СТ	: Logo
CNY17-X	: Part Number
Υ	: Fiscal Year
WW	: Work Week
D	: Manufacturing Code



## **Ordering Information**

# CNY17-X(Y)(Z)-G, CNY17F-X(Y)(Z)-G

X = (1,2,3,4)

Y = Lead form option (S, SL, M or none)

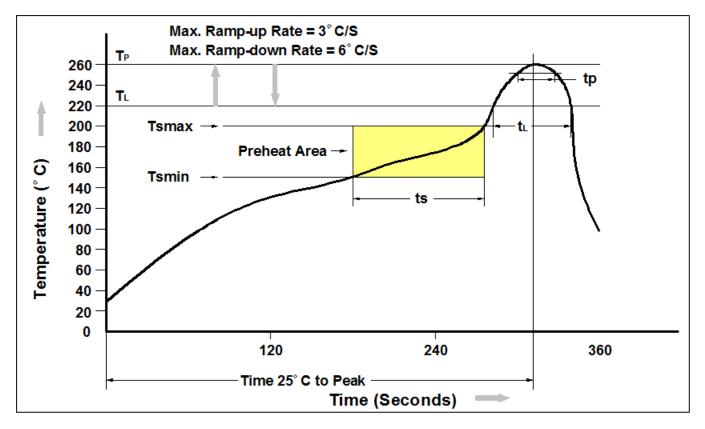
Z = Tape and reel option (TA, TB or none)

G= Material option (G: Green, None: Non-green)

Option Description		Quantity
None	None Standard 6 Pin Dip	
М	Wide Lead Forming	50Units/Tube
S(TA)	Surface Mount Lead Forming – With Option A Taping	1000 Units/Reel
S(TB)	Surface Mount Lead Forming – With Option B Taping	1000 Units/Reel
SL(TA)	Surface Mount Lead Forming(Low Profile) – With Option A Taping	1000 Units/Reel
SL(TB)	Surface Mount Lead Forming(Low Profile) – With Option B Taping	1000 Units/Reel



### **Reflow Profile**



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to tթ)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate $(T_P \text{ to } T_L)$	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



#### DISCLAIMER

CT MICRO RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. CT MICRO DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

DISCOLORATION MIGHT OCCUR ON THE PACKAGE SURFACE AFTER SOLDERING, REFLOW OR LONG TERM USE. THIS DOES NOT IMPACT THE PRODUCT PERFORMANCE NOR THE PRODUCT RELIABILITY.

CT MICRO ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT EXPRESS WRITTEN APPROVAL OF CT MICRO INTERNATIONAL CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instruction for use provided in the labelling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.